

NE/SE5535

Dual High Slew Rate Op Amp

Product Specification

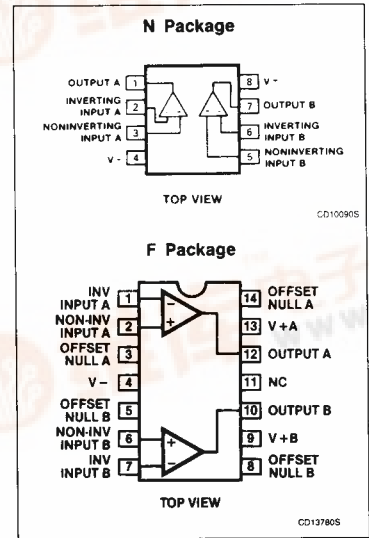
DESCRIPTION

The NE/SE5535 is a new generation operational amplifier featuring high slew rates combined with improved input characteristics. The 5535 is a dual configuration. Internally compensated for unity gain, the SE5535 features a guaranteed unity gain slew rate of $10V/\mu s$ with 4mV maximum offset voltage. Industry standard pinout and internal compensation allow the user to upgrade system performance by directly replacing general purpose amplifiers, such as 747 and 1558.

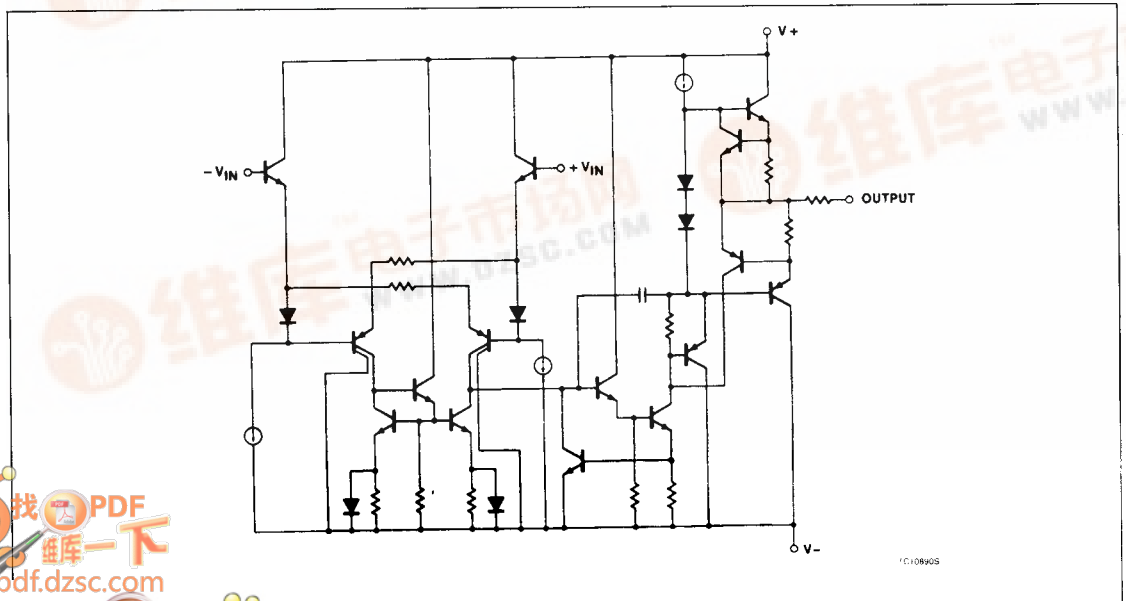
FEATURES

- $15V/\mu s$ unity gain slew rate
- Internal frequency compensation
- Low input offset voltage — 2mV
- Low input bias current 80nA max
- Short-circuit protected
- Large common-mode and differential voltage ranges
- Pin compatibility $\frac{5535}{747, 1558}$
- Dual configuration
- Low noise current $0.15pA/\sqrt{Hz}$ typ.

PIN CONFIGURATION



EQUIVALENT SCHEMATIC (one amplifier)



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ORDERING INFORMATION

| DESCRIPTION | TEMPERATURE RANGE | ORDER CODE |
|-------------------|-------------------|------------|
| 8-Pin Plastic DIP | 0 to +70°C | NE5535N |
| 8-Pin Plastic DIP | -55°C to +125°C | SE5535N |
| 14-Pin Cerdip | 0 to +70°C | NE5535F |
| 14-Pin Cerdip | -55 to +125°C | SE5535F |

ABSOLUTE MAXIMUM RATINGS

| SYMBOL | PARAMETER | SE5535 | NE5535 | UNIT |
|------------|---|-------------|-------------|------|
| V_S | Supply voltage | ± 22 | ± 18 | V |
| P_D | Internal power dissipation ¹ | | | |
| | N package | 1275 | 1275 | mW |
| | F package | 1250 | 1250 | mW |
| V_{IN} | Differential input voltage | ± 30 | ± 30 | V |
| V_{IN} | Input voltage ² | ± 15 | ± 15 | V |
| T_A | Operating temperature range | -55 to +125 | 0 to +70 | °C |
| T_{STG} | Storage temperature range | -65 to +150 | -65 to +150 | °C |
| T_{SOLD} | Lead soldering temperature (10sec max) | 300 | 300 | °C |
| I_{SC} | Output short-circuit ³ | Indefinite | Indefinite | |

NOTES:

- Rating applies at $T_A = 25^\circ\text{C}$ for thermal resistances junction to ambient of 98°C/W and 100°C/W for N and F packages, respectively. Maximum junction temperature is 150°C .
- For supply voltages less than $\pm 15\text{V}$, the absolute maximum input voltage is equal to the supply voltage.
- Short-circuit may be to ground or either supply. Rating applies to 125°C case temperature or 75°C ambient temperature.



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DC ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, $V_S = \pm 15\text{V}$, unless otherwise specified.*

| SYMBOL | PARAMETER | TEST CONDITIONS | SE5535 | | | NE5535 | | | UNIT |
|--------------------------|------------------------------|---|----------|----------|-----|----------|----------|------------------------------|------------------------|
| | | | Min | Typ | Max | Min | Typ | Max | |
| V_{OS} | Input offset voltage | $R_S \leq 10\text{k}\Omega$ $R_S \leq 10\text{k}\Omega$, over temp. | | 0.7 | 4.0 | | 2.0 | 6.0 | mV |
| | | | | | 5.0 | | 7.0 | | mV |
| $\Delta V_{OS}/\Delta T$ | | $R_S = 0\Omega$, over temp. | | 4.0 | | 6.0 | | $\mu\text{V}/^\circ\text{C}$ | |
| I_{OS} | Input offset current | Over temp. | | 5 | 20 | | 15 | 40 | nA |
| | | | | | 40 | | 80 | | nA |
| $\Delta I_{OS}/\Delta T$ | | Over temp. | | 25 | | 40 | | $\mu\text{A}/^\circ\text{C}$ | |
| I_B | Input bias current | Over temp. | | 45 | 80 | | 65 | 150 | nA |
| | | | | | 200 | | 200 | | nA |
| $\Delta I_B/\Delta T$ | | Over temp. | | 50 | | 80 | | $\mu\text{A}/^\circ\text{C}$ | |
| V_{CM} | Common-mode voltage range | | ± 12 | ± 13 | | ± 12 | ± 13 | V | |
| CMRR | Common-mode rejection ratio | $R_S \leq 10\text{k}\Omega$, over temp. | 70 | 90 | | 70 | 90 | dB | |
| PSRR | Power supply rejection ratio | $R_S \leq 10\text{k}\Omega$, over temp. | | 30 | 150 | | 30 | 150 | $\mu\text{V}/\text{V}$ |
| R_{IN} | Input resistance | | 3 | 10 | | 1 | 6 | $\text{M}\Omega$ | |
| A_{VOL} | Large-signal voltage gain | $R_L \geq 2\text{k}\Omega$, $V_{OUT} = \pm 10\text{V}$ $R_L = 2\text{k}\Omega$, $V_{OUT} = \pm 10\text{V}$, over temp. | 50 | 500 | | 50 | 500 | | V/mV |
| | | | 25 | | | 25 | | | V/mV |
| V_{OUT} | Output voltage | $R_L \geq 2\text{k}\Omega$, over temp. $R_L \geq 10\text{k}\Omega$, over temp. | ± 10 | ± 13 | | ± 10 | ± 13 | | V |
| | | | ± 12 | ± 14 | | ± 12 | ± 14 | | V |
| I_{CC} | Supply current | Per amplifier Per amplifier, over temp. | | 1.8 | 2.8 | | 1.8 | 2.8 | mA |
| | | | | 2 | 3.3 | | 2 | 2.8 | mA |
| P_D | Power dissipation | Per amplifier Per amplifier, over temp. | | 54 | 84 | | 54 | 84 | mW |
| | | | | 60 | 99 | | 60 | 84 | mW |
| I_{SC} | Output short-circuit current | | 10 | 25 | 50 | 10 | 25 | 50 | mA |
| R_{OUT} | Output resistance | | | 100 | | | 100 | | Ω |

NOTE:

- * Temperature range:
SE types $-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$
NE types $0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$

AC ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise specified.

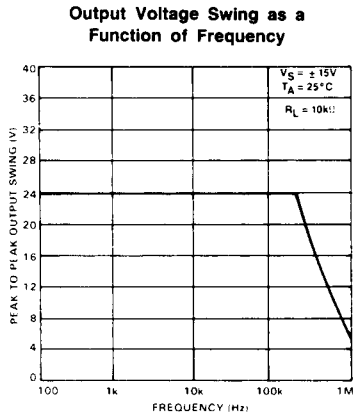
| SYMBOL | PARAMETER | TEST CONDITIONS | SE5535 | | | NE5535 | | | UNIT |
|--------|--|---|--------|------|-----|--------|------|------------------|------------------------------|
| | | | Min | Typ | Max | Min | Typ | Max | |
| GBW | Gain bandwidth product | | | 1 | | | 1 | | MHz |
| t_R | Transient response Small-signal rise time Small-signal overshoot | To 0.1% | | 0.25 | | | 0.25 | | μs |
| | | | | 6 | | | 6 | | % |
| t_S | Settling time | $R_L \geq 10\text{k}\Omega$, unity gain, non-inverting | | 3 | | | 3 | | μs |
| SR | Slew rate | | 10 | 15 | | 10 | 15 | V/ μs | |
| | Input noise voltage | $f = 1\text{kHz}$, $T_A = 25^\circ\text{C}$ | | 30 | | | 30 | | $\text{nV}/\sqrt{\text{Hz}}$ |



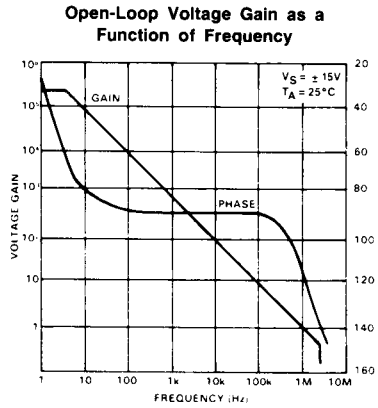
Dual High Slew Rate Op Amp

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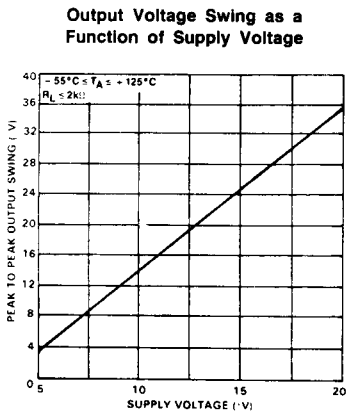
TYPICAL PERFORMANCE CHARACTERISTICS



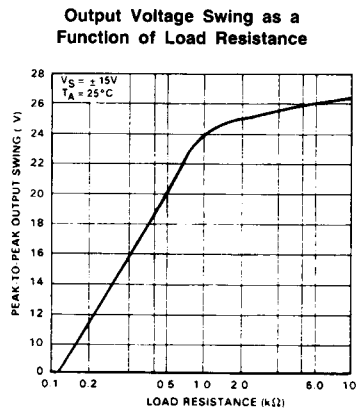
OP067805



OP067905



OP068005



OP068105

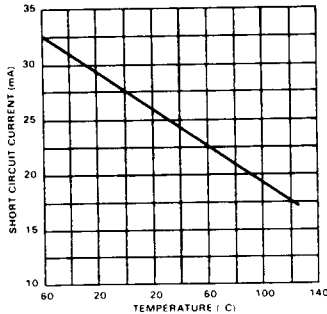


Dual High Slew Rate Op Amp

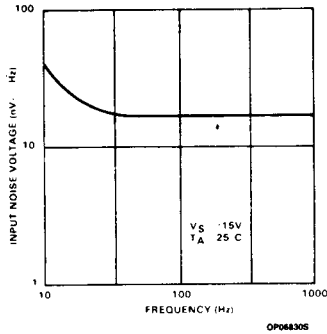
NE/SE5535

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

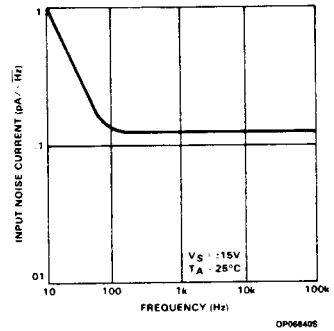
Output Short-Circuit Current as a Function of Ambient Temperature



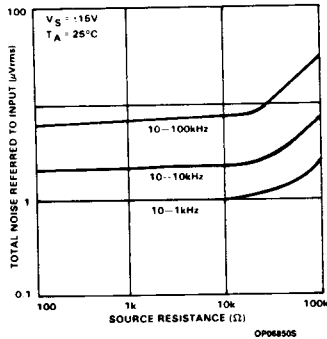
Input Noise Voltage as a Function of Frequency



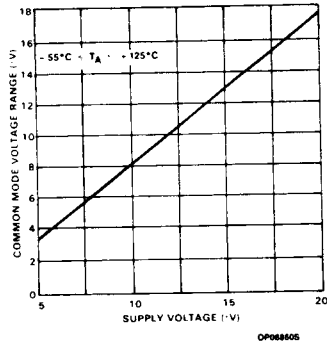
Input Noise Current as a Function of Frequency



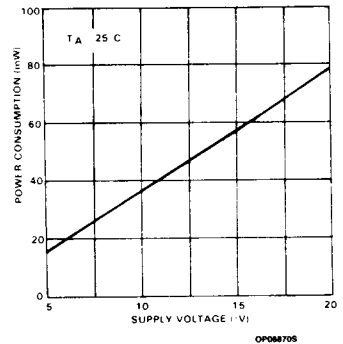
Broadband Noise for Various Bandwidths



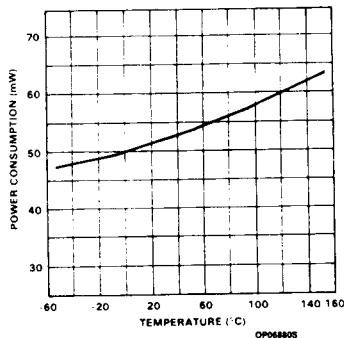
Input Common-Mode Voltage Range as a Function of Supply Voltage



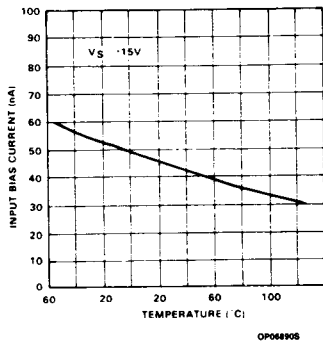
Power Consumption as a Function of Supply Voltage



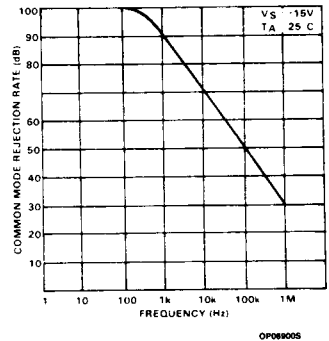
Power Consumption as a Function of Ambient Temperature



Input Bias Current as a Function of Ambient Temperature



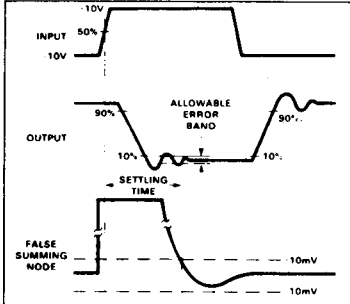
Common-Mode Rejection Ratio as a Function of Frequency



Dual High Slew Rate Op Amp

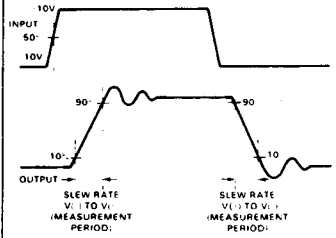
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VOLTAGE WAVEFORMS



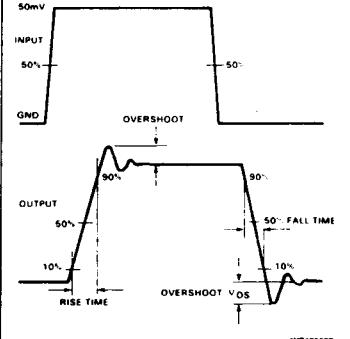
Settling Time Measurement

WF158108



Slew Rate Measurement

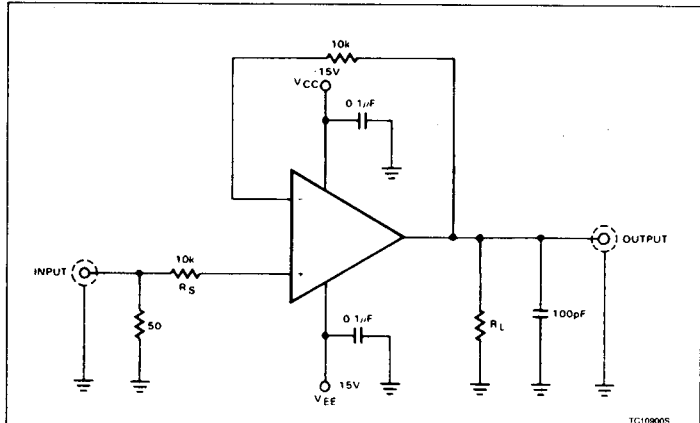
WF158208



Small-Signal Transient Response Definitions

WF158308

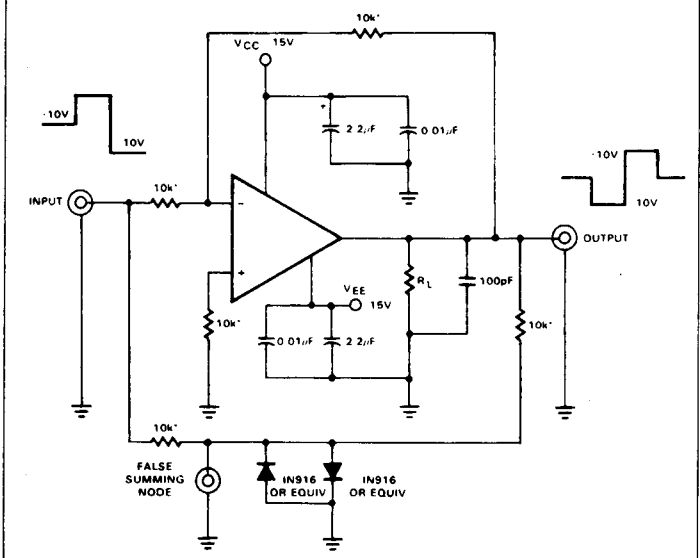
TEST CIRCUITS



TC109005

- NOTES:**
1. Pins not shown are not connected.
 2. All resistor values are typical and in ohms.

Slew Rate and Small-Signal Transient Response



TC108118

- NOTES:**
1. Pins not shown are not connected.
 2. All resistor values are typical and in ohms.
- *Match to within 0.01%.

Settling Time

Dual High Slew Rate Op Amp

NE/SE5535

INTRODUCTION

The NE5535 is a new generation monolithic op amp which features improved input characteristics. The device is compensated to unity gain and has a minimum guaranteed unity gain slew rate of 10V/μs. This is achieved by employing a clamped super beta input stage which has lower input bias current.

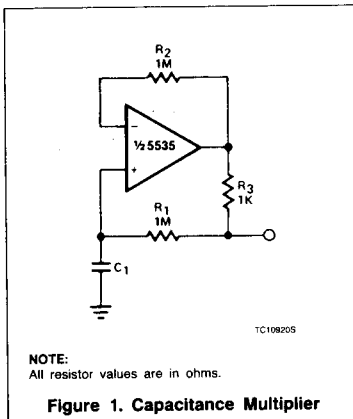


Figure 1. Capacitance Multiplier

APPLICATIONS

These improved parameters can be put to good use in applications such as sample and hold circuits which require low input current and in voltage-follower circuits which require high slew rates. The circuit that follows will yield maximum small-signal transient response and slew rate for the NE5535 at unity gain.

It is always good practice in designing a system to use dual tracking regulators to power the dual-supply op amps. This will

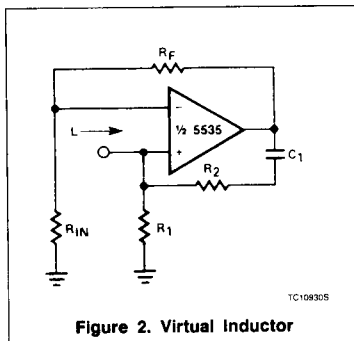


Figure 2. Virtual Inductor

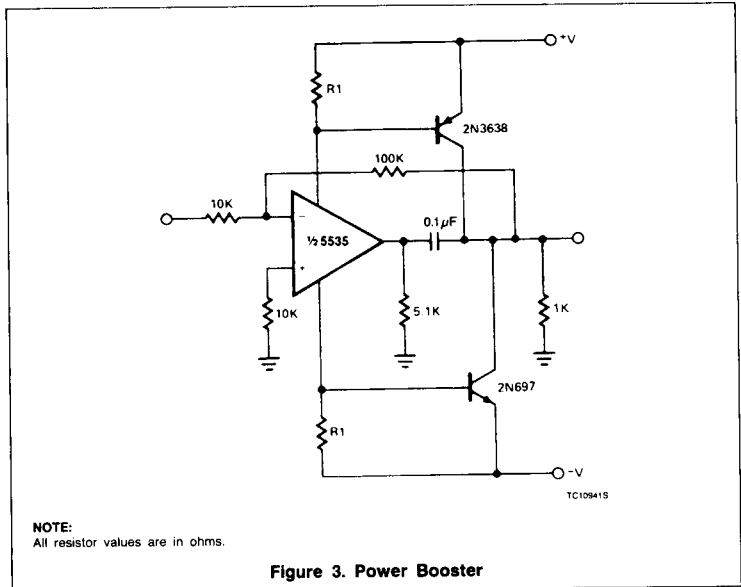


Figure 3. Power Booster

guarantee the positive and negative supply voltage will be equal during power-up. With the NE5535, it is possible to degrade the input circuit characteristics by not applying the power supplies simultaneously. The NE5535 is capable of directly replacing the μA741 with higher input resistance which will improve such designs as active filters, sample and hold, as well as voltage-followers.

The NE5535 can be used either with single or split power supplies.

Capacitance Multiplier

The circuit in Figure 1 can be used to simulate large capacitances using small value components. With the values shown and $C = 10\mu\text{F}$, an effective capacitance of $10,000\mu\text{F}$ was obtained. The Q available is limited by the effective series resistance. So R1 should be as large as practical.

Simulated Inductor

With a constant current excitation, the voltage dropped across an inductance increases with frequency. Thus, an active device whose output increases with frequency can be characterized as an inductance. The circuit of Figure 2 yields such a response with the effective inductance being equal to: $L = R_1 R_2 C$

The Q of this inductance depends upon R1 being equal to R2. At the same time, however, the positive and negative feedback paths of the amplifier are equal leading to the distinct

possibility of instability at high frequencies. R1 should therefore always be slightly smaller than R2 to assure stable operation.

Power Amplifier

For most applications, the available power from op amps is sufficient. There are times when more power handling capability is necessary. A simple power booster capable of driving moderate loads is offered in Figure 3.

The circuit as shown uses an NE5535 device. Other amplifiers may be substituted only if R1 values are changed because of the I_{CC} current required by the amplifier. R1 should be calculated from the expression

$$R_1 = \frac{600\text{mV}}{I_{CC}}$$

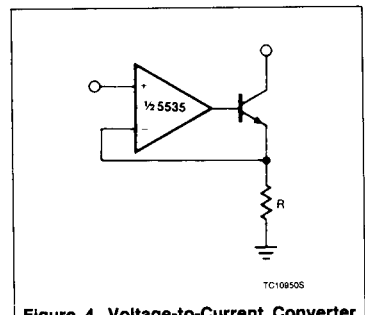


Figure 4. Voltage-to-Current Converter

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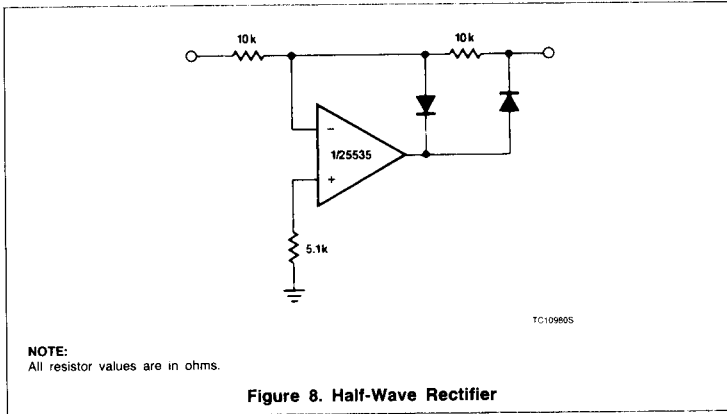


Figure 8. Half-Wave Rectifier

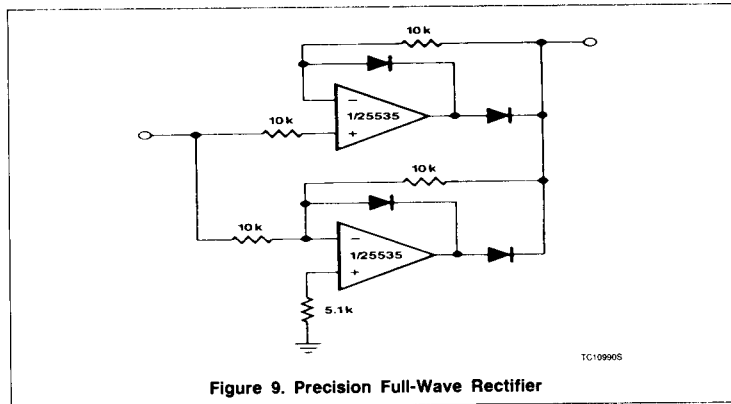
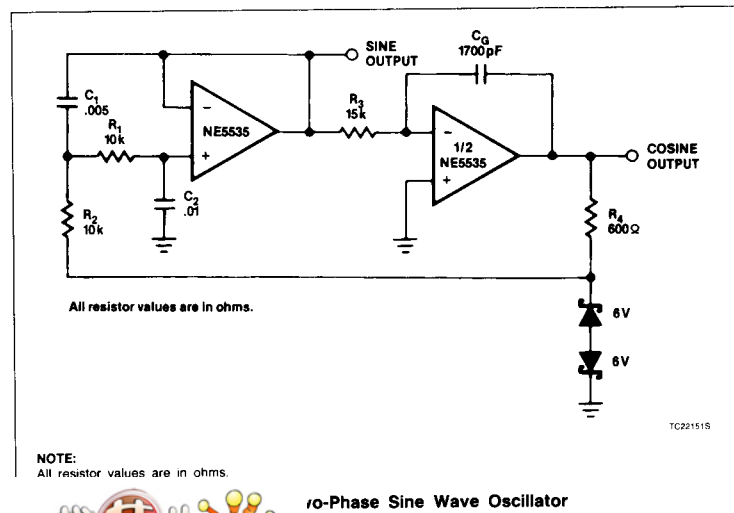


Figure 9. Precision Full-Wave Rectifier



Two-Phase Sine Wave Oscillator

Precision Full-Wave Rectifier

The circuit in Figure 9 provides accurate full-wave rectification. The output impedance is low for both input polarities, and the errors are small at all signal levels. Note that the output will not sink heavy currents, except a small amount through the 10kΩ resistors. Therefore, the load applied should be referenced to ground or a negative voltage. Reversal of all diode polarities will reverse the polarity of the output. Since the outputs of the amplifiers must slew through two diode drops when the input polarity changes, 741 type devices give 5% distortion at about 300Hz.

Two-Phase Sine Wave Oscillator

The circuit (refer to Figure 10) uses a 2-pole pass Butterworth, followed by a phase-shifting single-pole stage, fed back through a voltage limiter to achieve sine and cosine outputs. The values shown using the μA741 amplifiers give about 1.5% distortion at the sine output and about 3% distortion at the cosine output. By careful trimming of CG and/or the limiting network, better distortion figures are possible. The component values shown give a frequency of oscillation of about 2kHz. The values can be readily selected for other frequencies. The NE5535 should be used at higher frequencies to reduce distortion due to slew limiting.